

This technology is currently not available for licensing

Tech ID: 32268

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ [Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation](#)
- ▶ [III-Nitride-Based Vertical Cavity Surface Emitting Laser \(VCSEL\) with a Dielectric P-Side Lens](#)
- ▶ [Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide](#)
- ▶ [Methods to Produce and Recycle Substates for III-Nitride Materials with Electrochemical Etching](#)
- ▶ [III-Nitride Tunnel Junction with Modified Interface](#)
- ▶ [Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices](#)
- ▶ [\(In,Ga,Al\)N Optoelectronic Devices with Thicker Active Layers for Improved Performance](#)
- ▶ [Thermally Stable, Laser-Driven White Lighting Device](#)
- ▶ [Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices](#)
- ▶ [A Method To Lift-Off Nitride Materials With Electrochemical Etch](#)
- ▶ [Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs](#)
- ▶ [High-Intensity Solid State White Laser Diode](#)
- ▶ [Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact](#)
- ▶ [Epitaxial Light Control Features in Light Emitting Diodes](#)
- ▶ [High-Efficiency Vertical Cavity Surface Emitting Laser Fabrication](#)
- ▶ [A Wafer-Scale, Low Defect Density Strain Relaxed Template for III-Nitride-Based High Efficiency and High-Power Devices](#)
- ▶ [High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template](#)
- ▶ [III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture](#)